

Inverter Grade Thyristors (Hockey PUK Version), 330 A


A-PUK (TO-200AB)
FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- International standard case A-PUK (TO-200AB)
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**
PRIMARY CHARACTERISTICS

| | |
|-----------------------|------------------|
| Package | A-PUK (TO-200AB) |
| Circuit configuration | Single SCR |
| $I_{T(AV)}$ | 330 A |
| V_{DRM}/V_{RRM} | 1000 V, 1200 V |
| V_{TM} | 2.07 V |
| I_{TSM} at 50 Hz | 4680 A |
| I_{TSM} at 60 Hz | 4900 A |
| I_{GT} | 200 mA |
| T_C/T_{hs} | 55 °C |

TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER | TEST CONDITIONS | VALUES | UNITS |
|-------------------|-----------------|--------------|-------------------|
| $I_{T(AV)}$ | | 330 | A |
| | T_{hs} | 55 | °C |
| $I_{T(RMS)}$ | | 610 | A |
| | T_{hs} | 25 | °C |
| I_{TSM} | 50 Hz | 4680 | A |
| | 60 Hz | 4900 | |
| i^2t | 50 Hz | 110 | kA ² s |
| | 60 Hz | 100 | |
| V_{DRM}/V_{RRM} | | 1000 to 1200 | V |
| t_q | Range | 15 to 30 | μs |
| T_J | | -40 to 125 | °C |

ELECTRICAL SPECIFICATIONS
VOLTAGE RATINGS

| TYPE NUMBER | VOLTAGE CODE | V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK VOLTAGE V | V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V | I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA |
|--------------|--------------|--|--|--|
| VS-ST173C..C | 10 | 1000 | 1100 | 40 |
| | 12 | 1200 | 1300 | |



| CURRENT CARRYING CAPABILITY | | | | | | | |
|----------------------------------|-----------|-----|-----------|------|-----------|------|-------|
| FREQUENCY | | | | | | | UNITS |
| 50 Hz | 760 | 660 | 1200 | 1030 | 5570 | 4920 | A |
| 400 Hz | 730 | 590 | 1260 | 1080 | 2800 | 2460 | |
| 1000 Hz | 600 | 490 | 1200 | 1030 | 1620 | 1390 | |
| 2500 Hz | 350 | 270 | 850 | 720 | 800 | 680 | |
| Recovery voltage V_r | 50 | | 50 | | 50 | | V |
| Voltage before turn-on V_d | V_{DRM} | | V_{DRM} | | V_{DRM} | | |
| Rise of on-state current di/dt | 50 | | - | | - | | A/μs |
| Heatsink temperature | 40 | 55 | 40 | 55 | 40 | 55 | °C |
| Equivalent values for RC circuit | 47/0.22 | | 47/0.22 | | 47/0.22 | | Ω/μF |

| ON-STATE CONDUCTION | | | | | |
|--|---------------|---|---------------------------|------------|--------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum average on-state current at heatsink temperature | $I_{T(AV)}$ | 180° conduction, half sine wave double side (single side) cooled | | 330 (120) | A |
| | | | | 55 (85) | °C |
| Maximum RMS on-state current | $I_{T(RMS)}$ | DC at 25 °C heatsink temperature double side cooled | | 610 | |
| Maximum peak, one half cycle, non-repetitive surge current | I_{TSM} | t = 10 ms | No voltage reapplied | 4680 | A |
| | | | | t = 8.3 ms | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | 3940 | |
| | | | | t = 8.3 ms | |
| Maximum I^2t for fusing | I^2t | t = 10 ms | No voltage reapplied | 110 | kA ² s |
| | | | | t = 8.3 ms | |
| | | t = 10 ms | 100 % V_{RRM} reapplied | 77 | |
| | | | | t = 8.3 ms | |
| Maximum $I^2\sqrt{t}$ for fusing | $I^2\sqrt{t}$ | t = 0.1 to 10 ms, no voltage reapplied | | 1100 | kA ² √s |
| Maximum peak on-state voltage | V_{TM} | $I_{TM} = 600$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse | | 2.07 | V |
| Low level value of threshold voltage | $V_{T(TO)1}$ | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 1.55 | |
| High level value of threshold voltage | $V_{T(TO)2}$ | $(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 1.61 | |
| Low level value of forward slope resistance | r_{t1} | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.87 | mΩ |
| High level value of forward slope resistance | r_{t2} | $(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum | | 0.77 | |
| Maximum holding current | I_H | $T_J = 25$ °C, $I_T > 30$ A | | 600 | mA |
| Typical latching current | I_L | $T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A | | 1000 | |

| SWITCHING | | | | | |
|--|---------|--|--|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum non-repetitive rate of rise of turned on current | di/dt | $T_J = T_J$ maximum, $V_{DRM} = \text{rated } V_{DRM}$, $I_{TM} = 2 \times di/dt$ | | 1000 | A/μs |
| Typical delay time | t_d | $T_J = 25$ °C, $V_{DM} = \text{rated } V_{DRM}$, $I_{TM} = 50$ A DC, $t_p = 1$ μs Resistive load, gate pulse: 10 V, 5 Ω source | | 1.1 | μs |
| Maximum turn-off time | minimum | t_q | $T_J = T_J$ maximum, $I_{TM} = 300$ A, commutating $di/dt = 20$ A/μs $V_R = 50$ V, $t_p = 500$ μs, dV/dt : see table in device code | 15 | |
| | maximum | | | 30 | |



| BLOCKING | | | | |
|--|-------------------------------------|--|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise of off-state voltage | dV/dt | T _J = T _J maximum, linear to 80 % V _{DRM} , higher value available on request | 500 | V/μs |
| Maximum peak reverse and off-state leakage current | I _{RRM} , I _{DRM} | T _J = T _J maximum, rated V _{DRM} /V _{RRM} applied | 40 | mA |

| TRIGGERING | | | | |
|---|--------------------|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | T _J = T _J maximum, f = 50 Hz, d% = 50 | 60 | W |
| Maximum average gate power | P _{G(AV)} | | 10 | |
| Maximum peak positive gate current | I _{GM} | T _J = T _J maximum, t _p ≤ 5 ms | 10 | A |
| Maximum peak positive gate voltage | + V _{GM} | | 20 | V |
| Maximum peak negative gate voltage | - V _{GM} | | 5 | |
| Maximum DC gate current required to trigger | I _{GT} | T _J = 25 °C, V _A = 12 V, R _a = 6 Ω | 200 | mA |
| Maximum DC gate voltage required to trigger | V _{GT} | | 3 | V |
| Maximum DC gate current not to trigger | I _{GD} | T _J = T _J maximum, rated V _{DRM} applied | 20 | mA |
| Maximum DC gate voltage not to trigger | V _{GD} | | 0.25 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | |
|--|---------------------|---|------------------|-----------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum operating junction temperature range | T _J | | -40 to 125 | °C |
| Maximum storage temperature range | T _{Stg} | | -40 to 150 | |
| Maximum thermal resistance, junction to heatsink | R _{thJ-hs} | DC operation single side cooled | 0.17 | K/W |
| | | DC operation double side cooled | 0.08 | |
| Maximum thermal resistance, case to heatsink | R _{thC-hs} | DC operation single side cooled | 0.033 | |
| | | DC operation double side cooled | 0.017 | |
| Mounting force, ± 10 % | | | 4900 (500) | N (kg) |
| Approximate weight | | | 50 | g |
| Case style | | See dimensions - link at the end of datasheet | A-PUK (TO-200AB) | |

| ΔR_{thJ-hs} CONDUCTION | | | | | | |
|---------------------------------------|-----------------------|-------------|------------------------|-------------|---|-------|
| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | | RECTANGULAR CONDUCTION | | TEST CONDITIONS | UNITS |
| | SINGLE SIDE | DOUBLE SIDE | SINGLE SIDE | DOUBLE SIDE | | |
| 180° | 0.015 | 0.016 | 0.011 | 0.011 | T _J = T _J maximum | K/W |
| 120° | 0.018 | 0.019 | 0.019 | 0.019 | | |
| 90° | 0.024 | 0.024 | 0.026 | 0.026 | | |
| 60° | 0.035 | 0.035 | 0.036 | 0.037 | | |
| 30° | 0.060 | 0.060 | 0.060 | 0.061 | | |

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

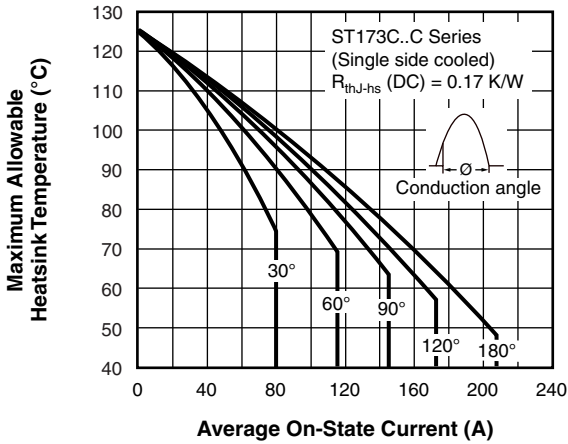


Fig. 1 - Current Ratings Characteristics

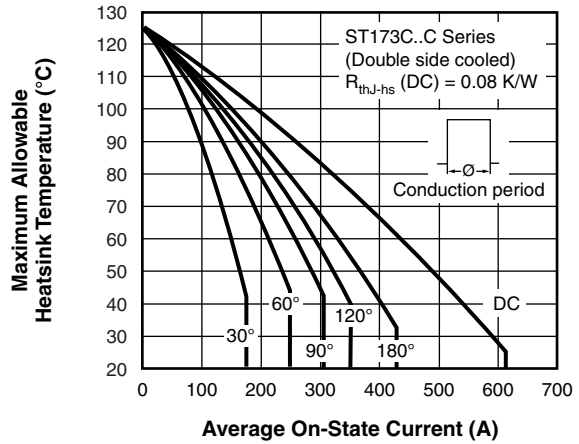


Fig. 4 - Current Ratings Characteristics

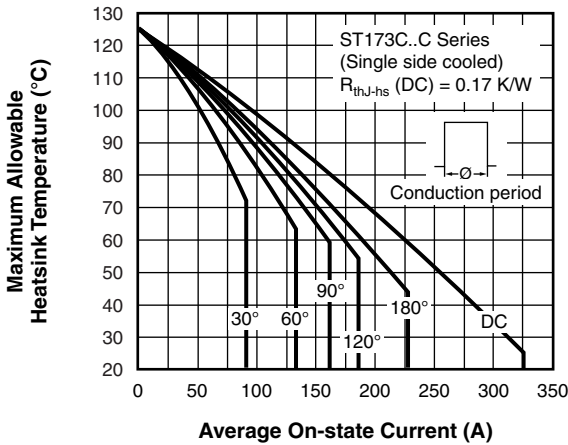


Fig. 2 - Current Ratings Characteristics

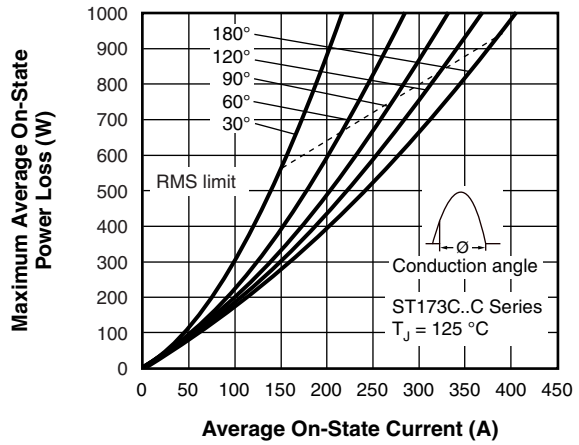


Fig. 5 - On-State Power Loss Characteristics

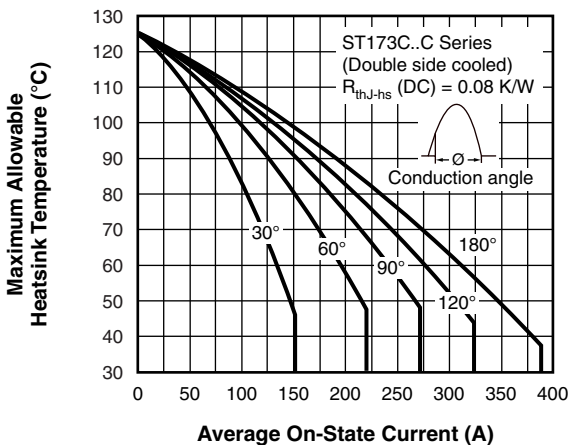


Fig. 3 - Current Ratings Characteristics

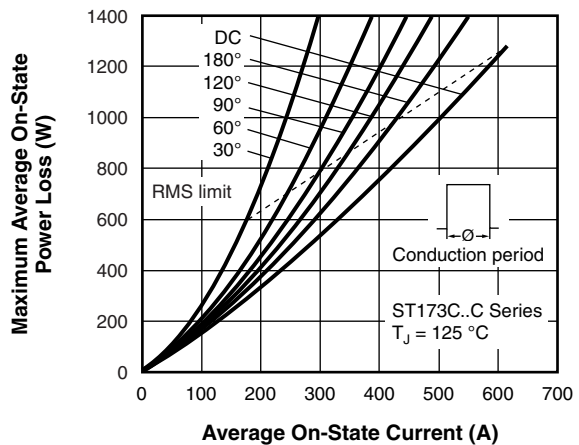


Fig. 6 - On-State Power Loss Characteristics

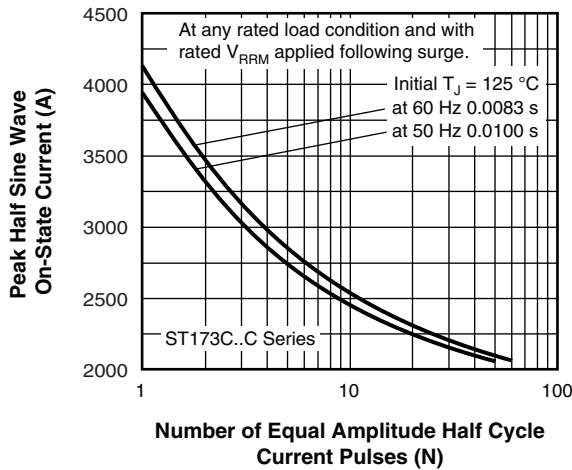


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

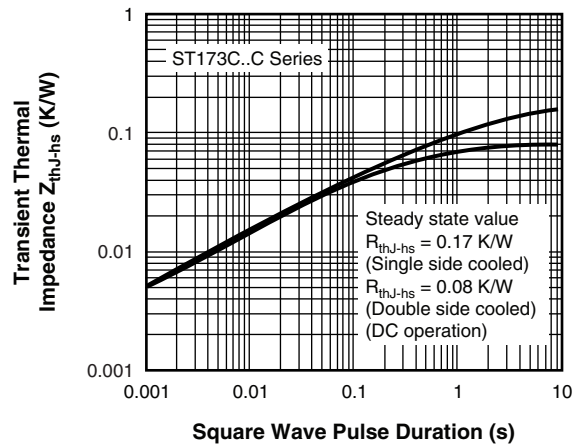


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

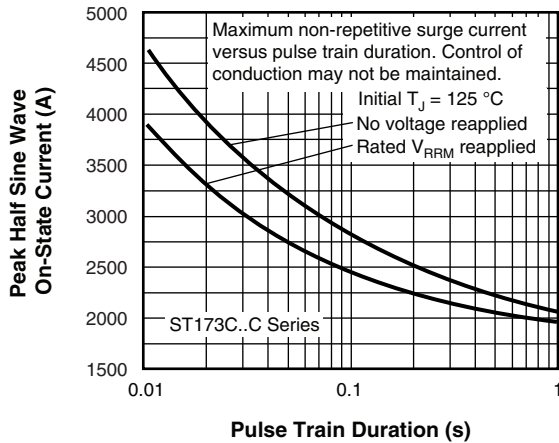


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

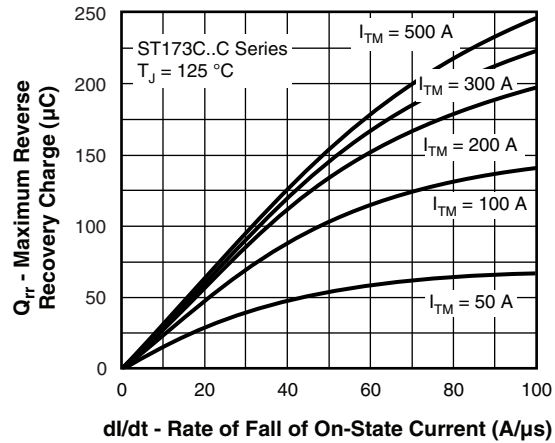


Fig. 11 - Reverse Recovered Charge Characteristics

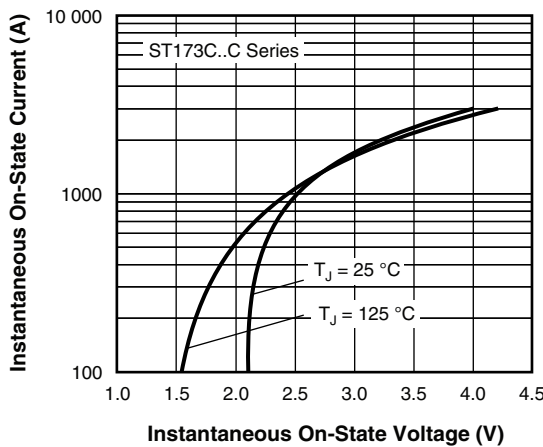


Fig. 9 - On-State Voltage Drop Characteristics

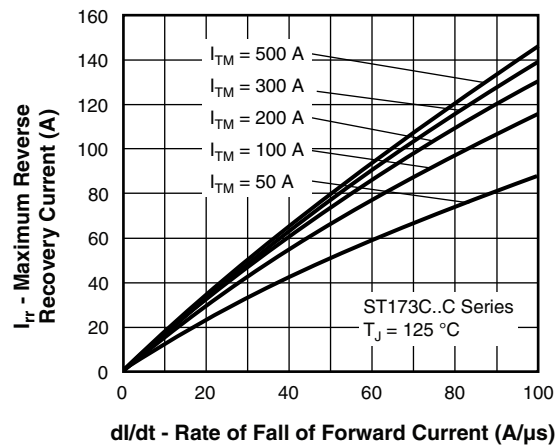


Fig. 12 - Reverse Recovered Current Characteristics

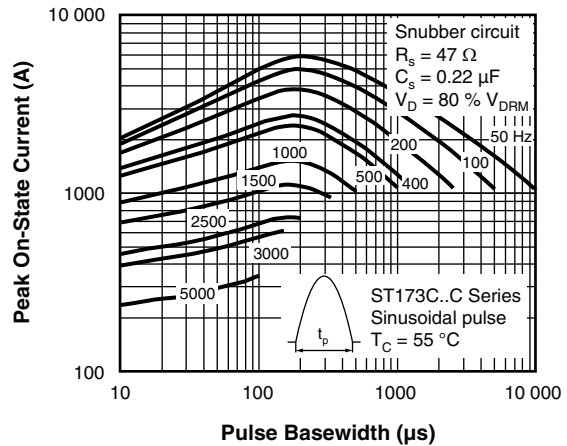
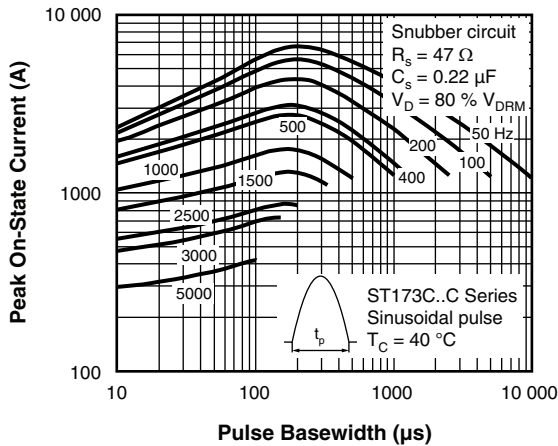


Fig. 13 - Frequency Characteristics

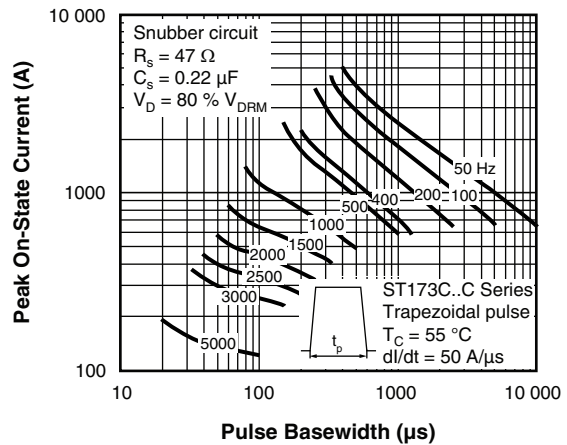
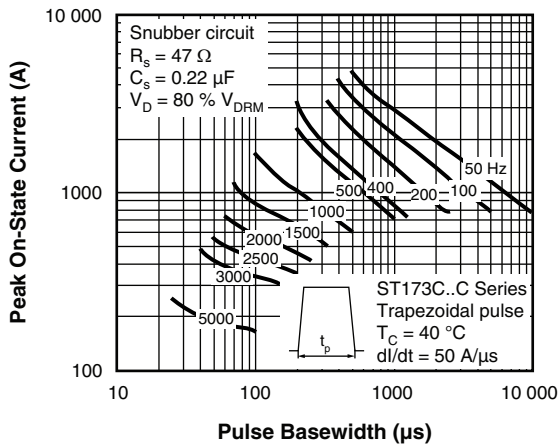


Fig. 14 - Frequency Characteristics

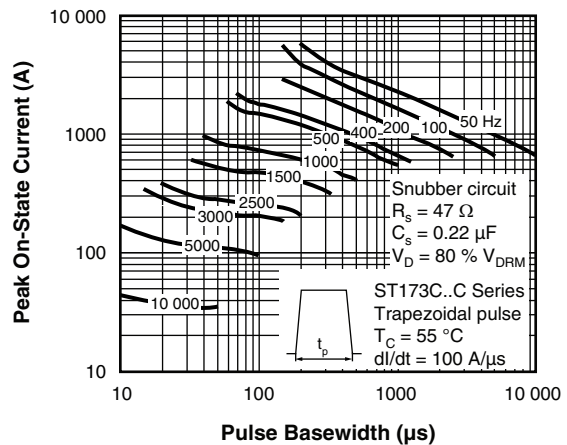
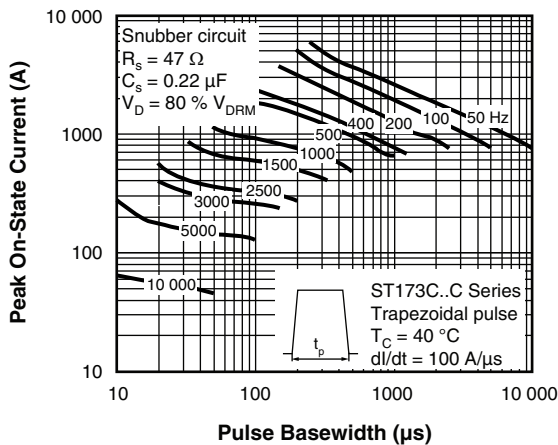


Fig. 15 - Frequency Characteristics

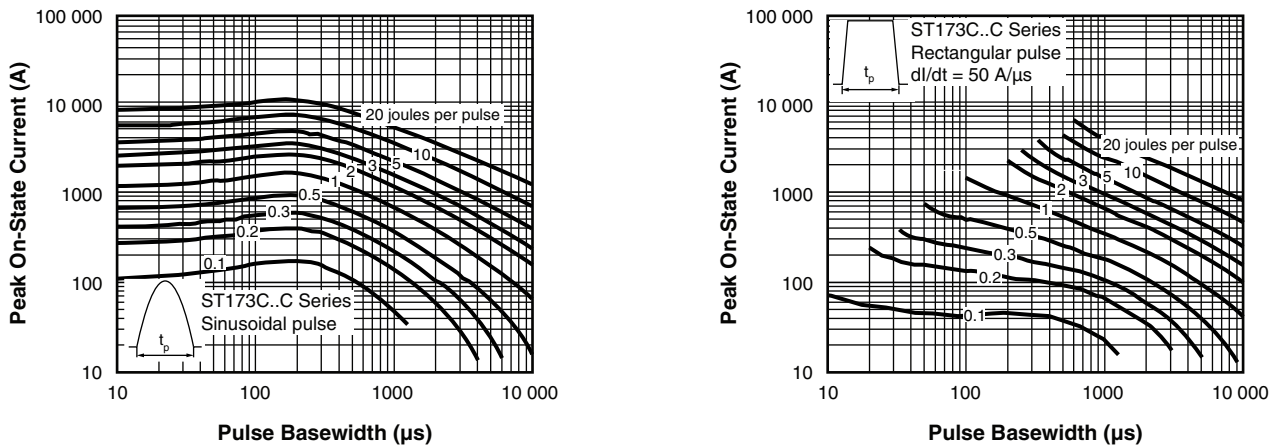


Fig. 16 - Maximum On-State Energy Power Loss Characteristics

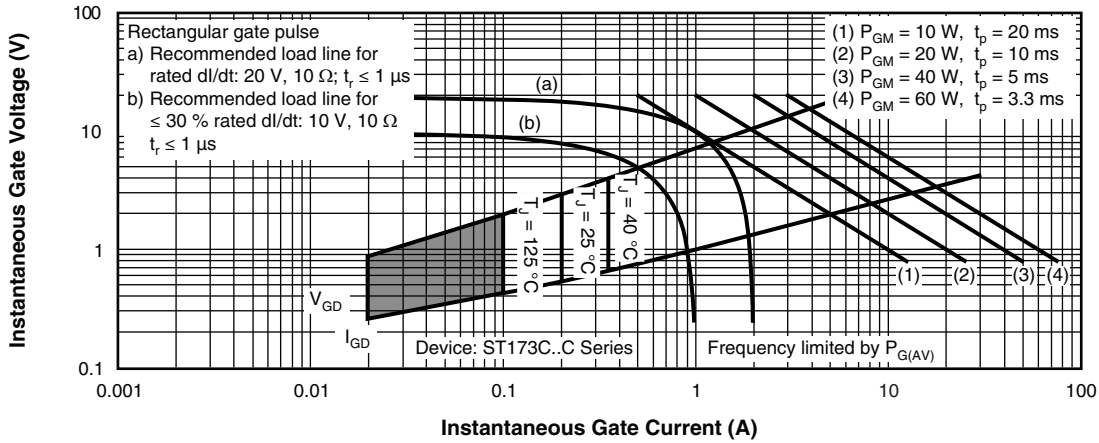
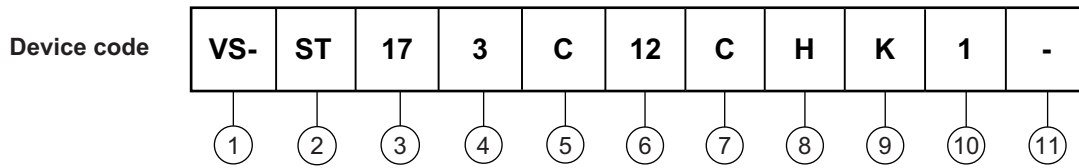


Fig. 17 - Gate Characteristics



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = fast turn-off
- 5** - C = ceramic PUK
- 6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 7** - C = PUK case A-PUK (TO-200AB)
- 8** - Reapplied dV/dt code (for t_q test condition)
- 9** - t_q code
- 10** - 0 = eyelet terminals
(gate and aux. cathode unsoldered leads)
1 = fast-on terminals
(gate and aux. cathode unsoldered leads)
2 = eyelet terminals
(gate and aux. cathode soldered leads)
3 = fast-on terminals
(gate and aux. cathode soldered leads)
- 11** - Critical dV/dt:
 - None = 500 V/ μ s (standard value)
 - L = 1000 V/ μ s (special selection)

| dV/dt - t_q combinations available | | | | | |
|--------------------------------------|----|----|-----|-----|-------------|
| dV/dt (V/ μ s) | 20 | 50 | 100 | 200 | 400 |
| t_q (μ s) | 15 | CL | -- | -- | -- |
| | 18 | CP | DP | EP | FP * |
| | 20 | CK | DK | EK | FK * |
| | 25 | CJ | DJ | EJ | FJ |
| | 30 | -- | DH | EH | FH |

* Standard part number.
All other types available only on request.

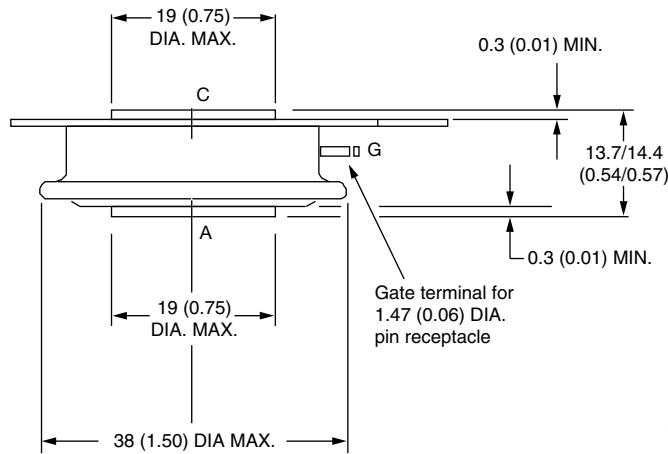
| LINKS TO RELATED DOCUMENTS | |
|----------------------------|--|
| Dimensions | www.vishay.com/doc?95074 |



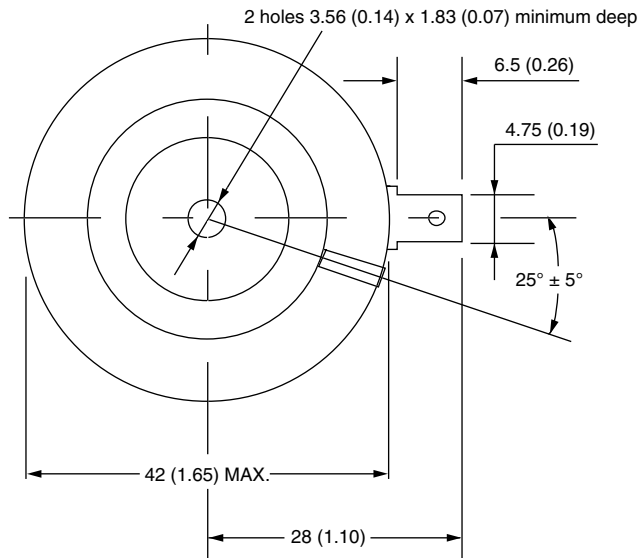
A-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate
Creepage distance: 7.62 (0.30) minimum
Strike distance: 7.12 (0.28) minimum



Note:
 A = Anode
 C = Cathode
 G = Gate



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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